

GenX3™ 600V IGBTs

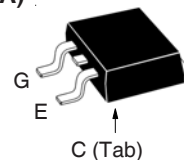
IXGA48N60A3
IXGP48N60A3
IXGH48N60A3

V_{CES} = 600V
I_{C110} = 48A
V_{CE(sat)} ≤ 1.35V

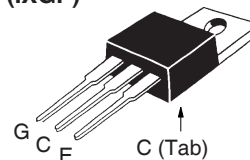
Ultra Low V_{sat} PT IGBTs for up to 5kHz switching

Symbol	Test Conditions	Maximum Ratings	
V _{CES}	T _J = 25°C to 150°C	600	V
V _{CGR}	T _J = 25°C to 150°C, R _{GE} = 1MΩ	600	V
V _{GES}	Continuous	±20	V
V _{GEM}	Transient	±30	V
I _{C25}	T _C = 25°C	120	A
I _{C110}	T _C = 110°C	48	A
I _{CM}	T _C = 25°C, 1ms	300	A
SSOA (RBSOA)	V _{GE} = 15V, T _{VJ} = 125°C, R _G = 5Ω Clamped Inductive Load	I _{CM} = 96 V _{CE} ≤ V _{CES}	A
P _C	T _C = 25°C	300	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	Maximum Lead Temperature for Soldering	300	°C
T _{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
F _C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
M _d	Mounting Torque (TO-220 & TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

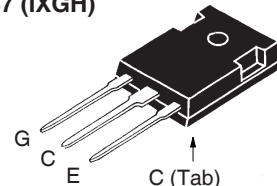
TO-263 (IXGA)



TO-220 (IXGP)



TO-247 (IXGH)



G = Gate C = Collector
 E = Emitter Tab = Collector

Features

- Optimized for Low Conduction Losses
- Square RBSOA
- High Current Handling Capability
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{CES}	I _C = 250μA, V _{GE} = 0V	600		V
V _{GE(th)}	I _C = 250μA, V _{CE} = V _{GE}	3.0		5.5 V
I _{CES}	V _{CE} = V _{CES} , V _{GE} = 0V T _J = 125°C			25 μA 250 μA
I _{GES}	V _{CE} = 0V, V _{GE} = ± 20V			±100 nA
V _{CE(sat)}	I _C = 32A, V _{GE} = 15V, Note 1	1.18	1.35	V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ unless otherwise specified)

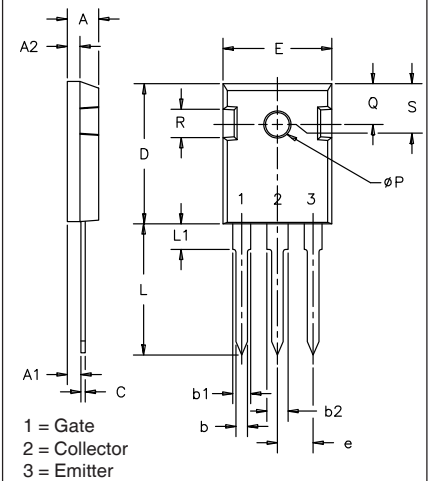
Characteristic Values

		Min.	Typ.	Max.	
g_{fs}	$I_C = 32\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	30	48		S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3190		pF
C_{oes}			175		pF
C_{res}			43		pF
Q_g	$I_C = 32\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		110		nC
Q_{ge}			21		nC
Q_{gc}			42		nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = 32\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		25		ns
t_{ri}			30		ns
E_{on}			0.95		mJ
$t_{d(off)}$			334		ns
t_{fi}			224		ns
E_{off}			2.9		mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$ $I_C = 32\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		24		ns
t_{ri}			30		ns
E_{on}			1.97		mJ
$t_{d(off)}$			545		ns
t_{fi}			380		ns
E_{off}			5.6		mJ
R_{thJC}				0.42	$^\circ\text{C/W}$
R_{thCK}	TO-220		0.50		$^\circ\text{C/W}$
	TO-247		0.21		$^\circ\text{C/W}$

Notes:

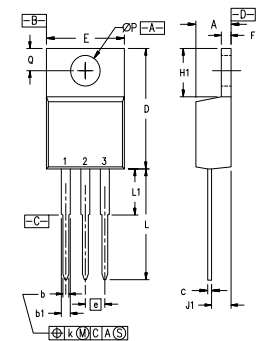
1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

TO-247 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
ϕP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

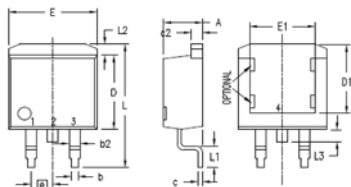
TO-220 Outline



Pins: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ϕP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-263 Outline



1 = Gate
2 = Collector
3 = Emitter
4 = Collector

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

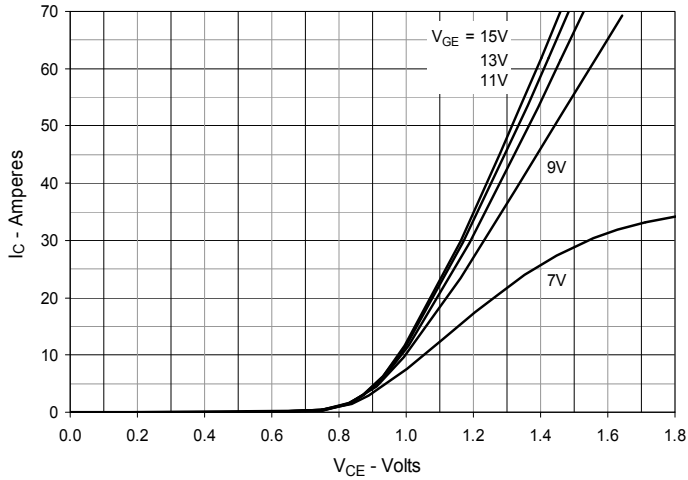


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

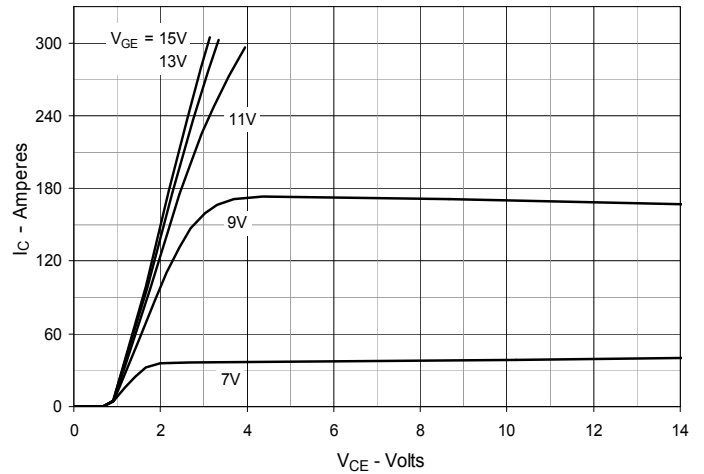


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

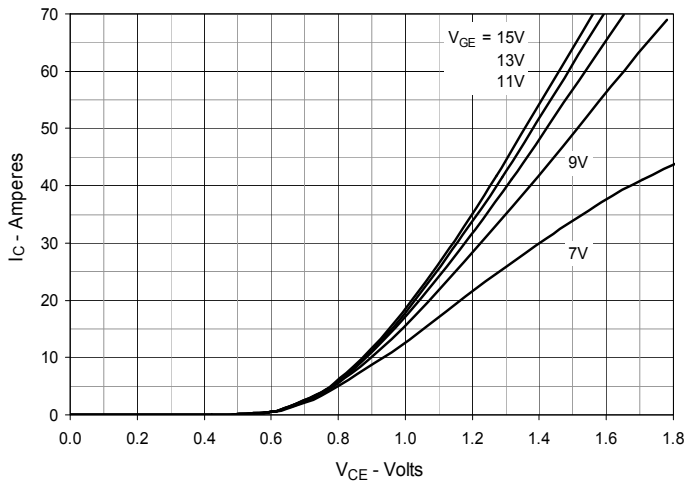


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

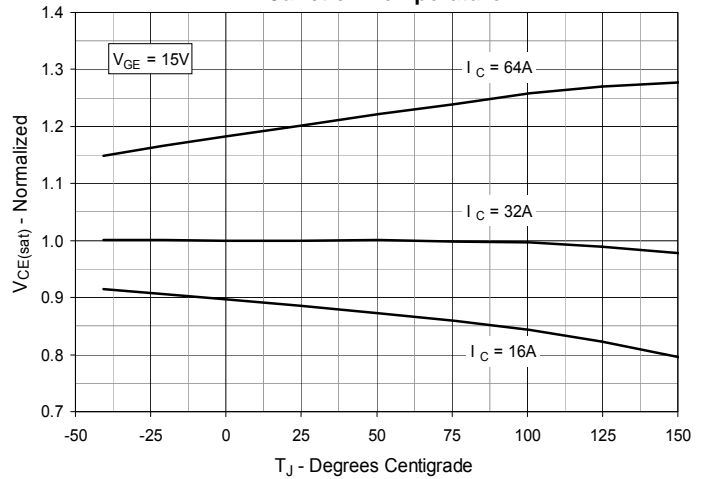


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

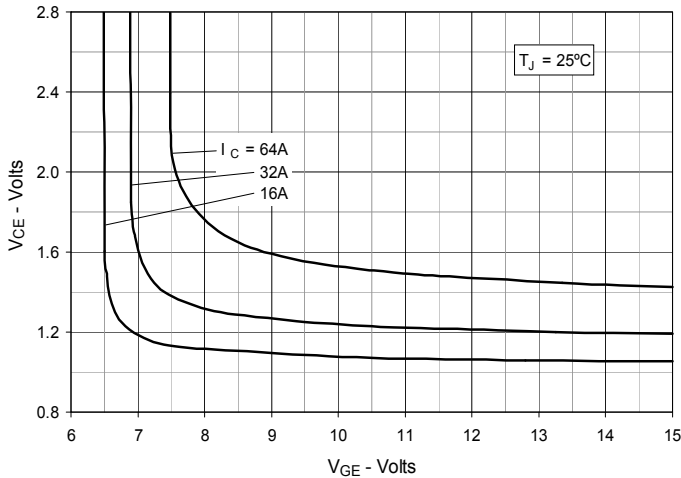


Fig. 6. Input Admittance



Fig. 7. Transconductance



Fig. 8. Gate Charge

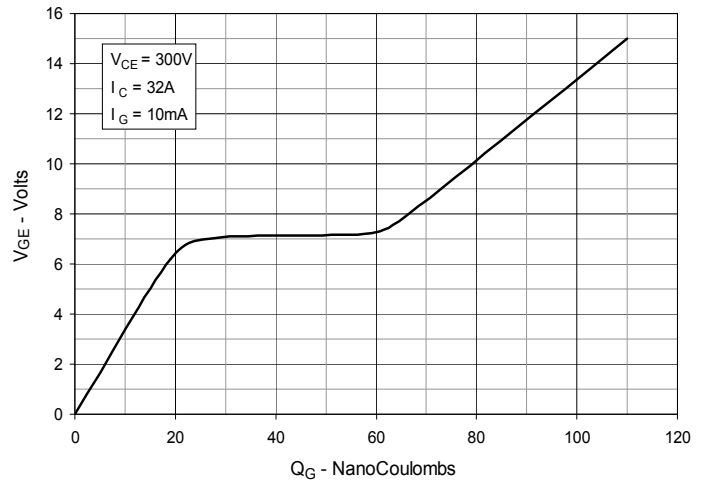


Fig. 9. Capacitance



Fig. 10. Reverse-Bias Safe Operating Area

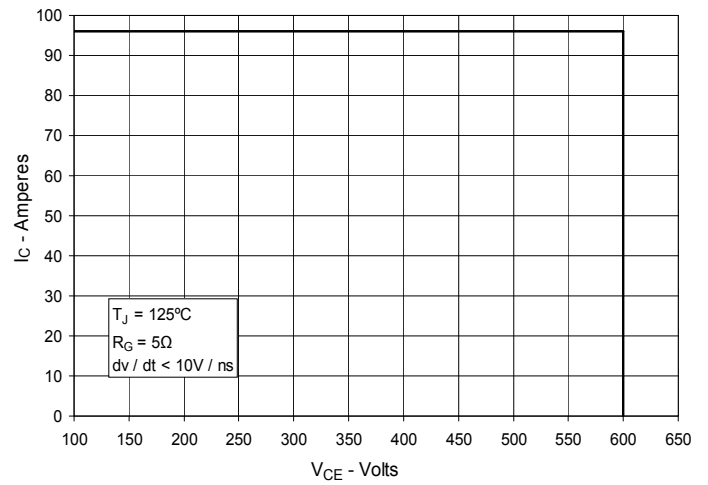


Fig. 11. Maximum Transient Thermal Impedance

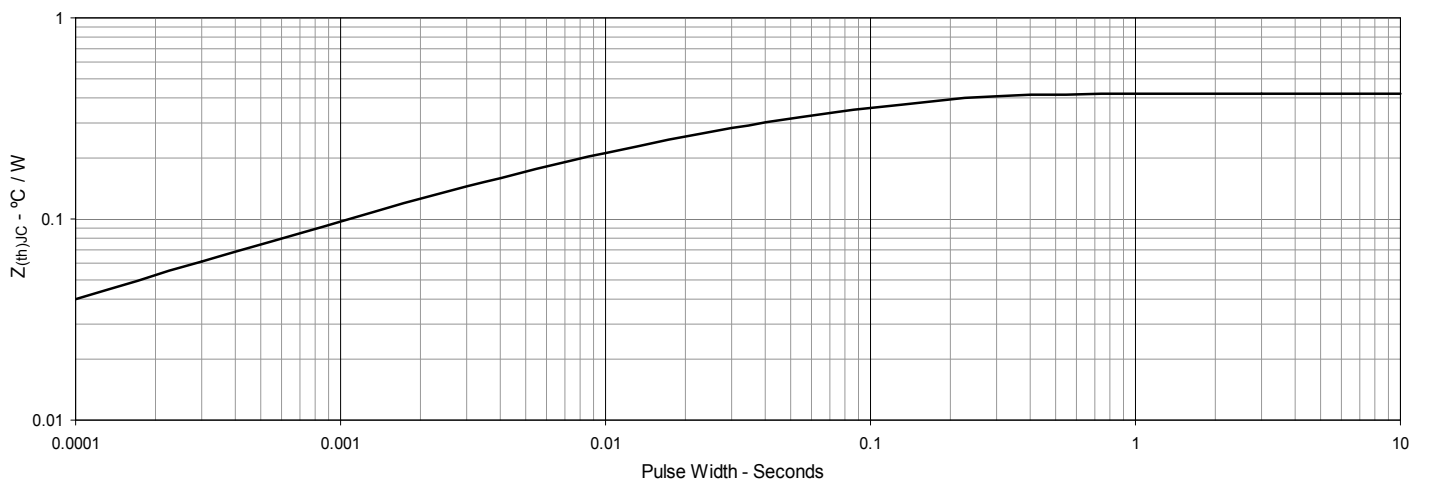


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance



Fig. 13. Inductive Switching Energy Loss vs. Collector Current



Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature



Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance



Fig. 16. Inductive Turn-off Switching Times vs. Collector Current



Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature



Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

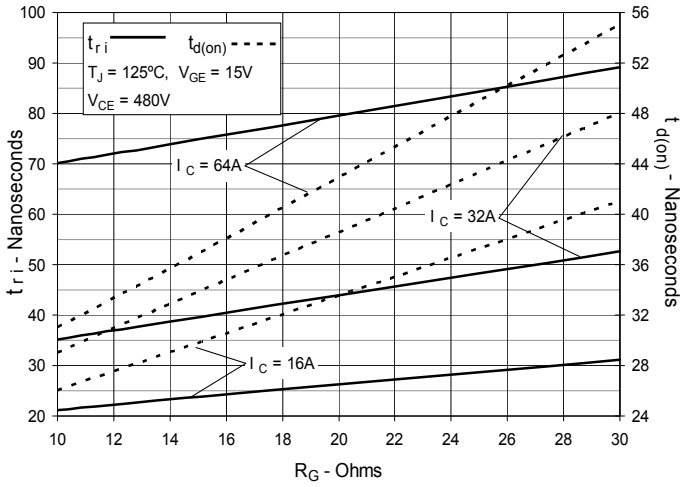


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

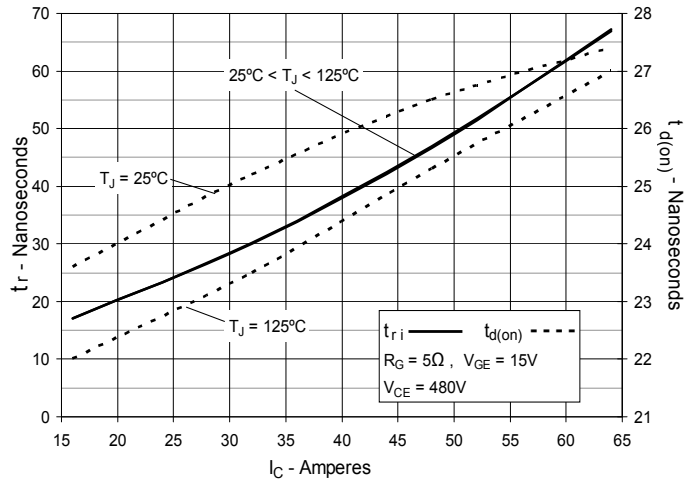
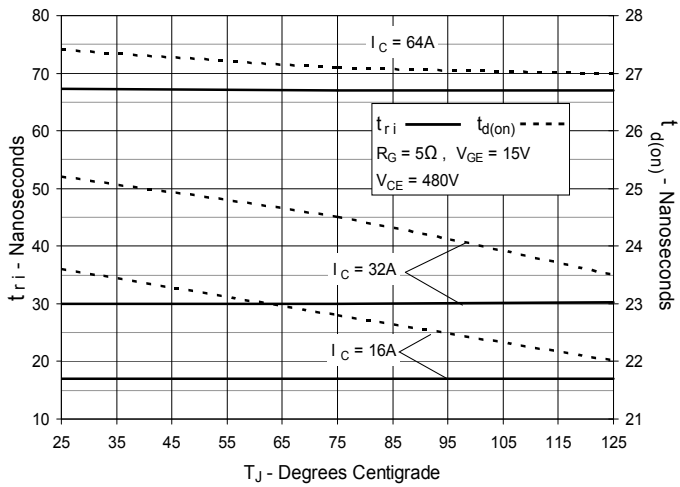


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature





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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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